

Abstract

A method for evaluating crystal defects of a silicon wafer comprising: etching a surface of the silicon wafer by immersing the wafer in an etching solution; and observing etch pits formed on the etched surface of the wafer, wherein the silicon wafer of which crystal defects are evaluated has low electrical resistivity of $1\ \Omega \cdot \text{cm}$ or less, and the etching solution is a mixture of hydrofluoric acid, nitric acid, acetic acid and water further including iodine or iodide, in which a volume ratio of nitric acid in the etching solution is the largest among volume ratios of hydrofluoric acid, nitric acid, acetic acid and water, and the etching solution is adjusted to have an etching rate of 100 nm/min or less for the silicon wafer. Thereby, there is provided a method for evaluating crystal defects of a silicon wafer with low electrical resistivity by using a chromium-free etching solution without toxic chromium with high capability of detecting defects.